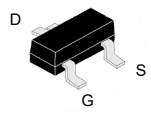
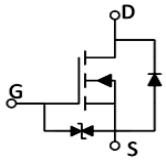
N-Channel MOSFET

2N7002K



SOT-23



SOT-23
SMD Plastic Package
RoHS compliant

Marking Code: 702

FEATURES:

1. High density cell design for low $R_{DS(ON)}$
2. Voltage controlled small signal switch
3. Rugged and reliable
4. High saturation current capability
5. ESD protected up to 2KV

APPLICATION: Designed for High Speed Pulse Amplifier and Drive Application

ABSOLUTE MAXIMUM RATINGS [1] (Ta = 25 ℃ Unless otherwise specified)

PARAMETER	SYMBOL	VALUE	UNIT
Drain-Source voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current	I_D	340	mA
Power Dissipation	P_D	350	mW
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	357	°C/W
Junction Temperature	T_J	150	°C
Storage Temperature	T_{STG}	-55 to +150	°C

ELECTRICAL CHARACTERISTICS [1] at (Ta = 25 ℃ Unless otherwise specified)

Off Characteristics

PARAMETER	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V,I_D=250μA	60	--	--	V
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	1	1.5	2.0	V
Gate –Source leakage current	I_{GSS}	V_{DS} = 0V, V_{GS} = ±20V	--	--	±5.0	μA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 48V, V_{GS} = 0V	--	--	1	μA
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS} = 4.5V, I_D = 200mA	--	1.3	2.0	Ω
		V_{GS} =10V, I_D = 500mA	--	0.9	1.9	
Drain-Source Diode Forward Voltage	V_{SD}	V_{GS} = 0V, I_S = 300mA	--	--	1.5	V
Recovered charge	Q_r	V_{GS} = 0V, I_S = 300mA, V_R = 25V, dIs/dt = -100A/μS	--	30	--	nC
Dynamic Characteristics						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 10V, f = 1.0MHz	--	--	40	pF
Output Capacitance	C_{oss}		--	--	30	
Reverse Transfer Capacitance	C_{rss}		--	--	10	
Switching Characteristics						
Turn-On Time	$t_{d(ON)}$	V_{GS}=10V,V_{DD}=50V,R_G=50Ω, R_{GS}=50Ω, R_L=250Ω	--	--	10	ns
Turn-Off Time	$t_{d(OFF)}$		--	--	15	
Reverse Recovery Time	t_{rr}	V_{GS}=0V,I_S=300mA, V_R=25V,dI_s/dt=-100A/μS		30	--	ns
Gate-Source Breakdown Voltage	BV_{GSO}	I_{gs} = ±1mA (Open Drain)	±21.5	--	±30	V

NOTES:

1. Pulse Test: Pulse Width ≤300μs, Duty Cycle ≤2%.
2. These parameters have no way to verify

TYPICAL CHARACTERISTICS CURVES

Fig 1: Output Characteristics

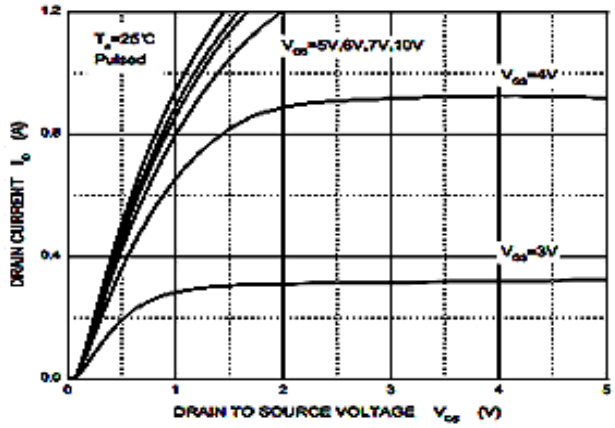


Fig 2: On Resistance vs Drain Current

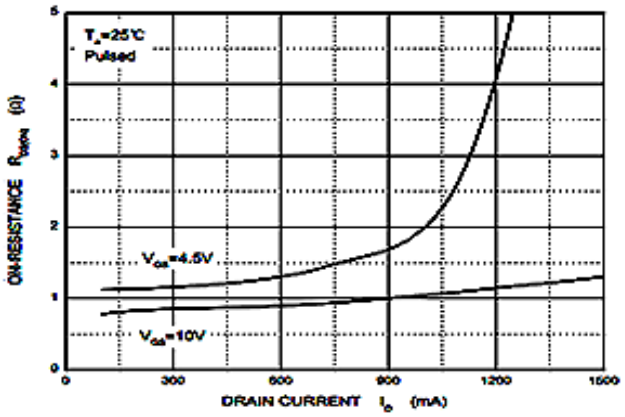


Fig 3: Source Current vs Source to Drain Voltage

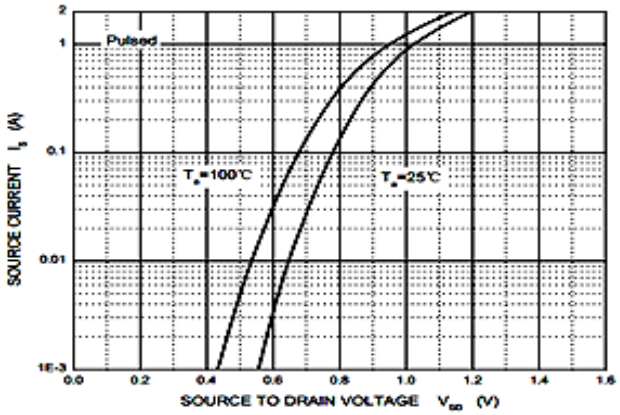


Fig 4: Transfer Characteristics

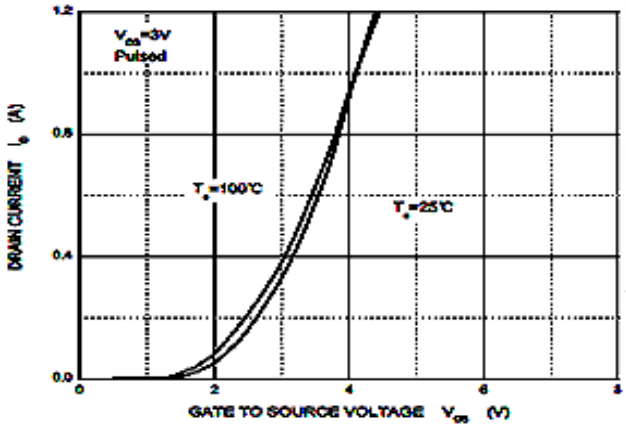


Fig 5: On Resistance vs Gate to Source Voltage

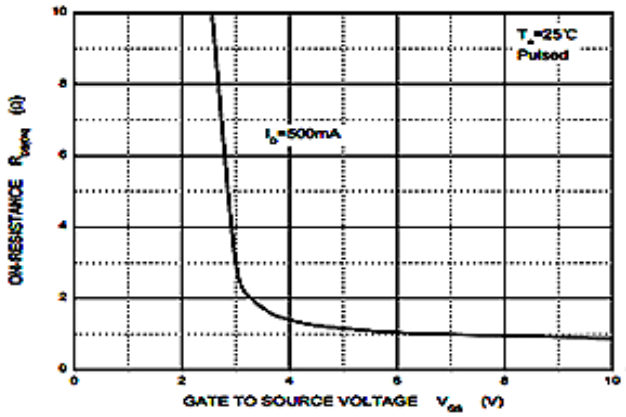
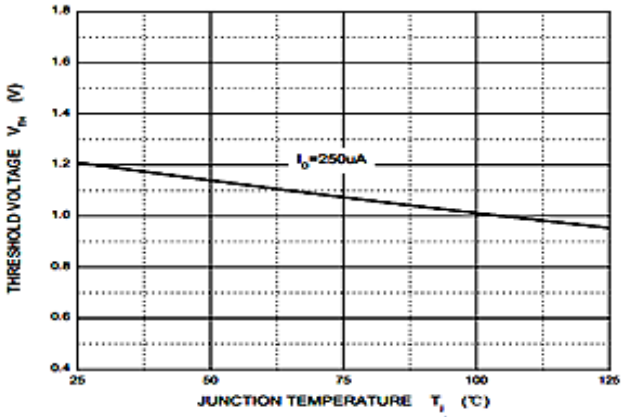
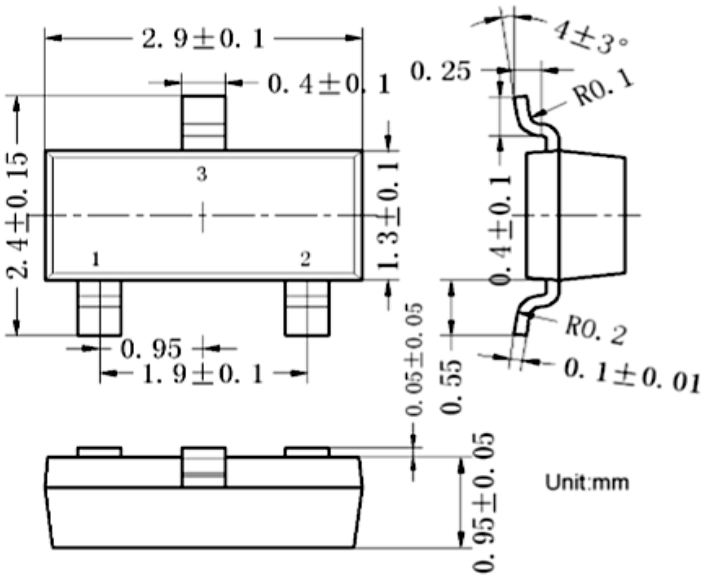


Fig 6: Threshold Voltage



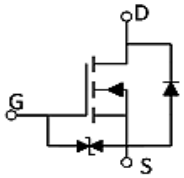
PACKAGE DETAILS

SOT-23 SMD Plastic Package

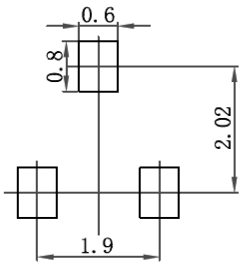


Pin Configuration

1. Gate
2. Source
3. Drain



SOT -23 Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.

Recommended Reflow Solder Profiles

The recommended reflow solder profiles for Pb and Pb-free devices are shown below.

Figure 1 shows the recommended solder profile for devices that have Pb-free terminal plating, and where a Pb-free solder is used.

Figure 2 shows the recommended solder profile for devices with Pb-free terminal plating used with leaded solder, or for devices with leaded terminal plating used with a leaded solder.

Figure 1

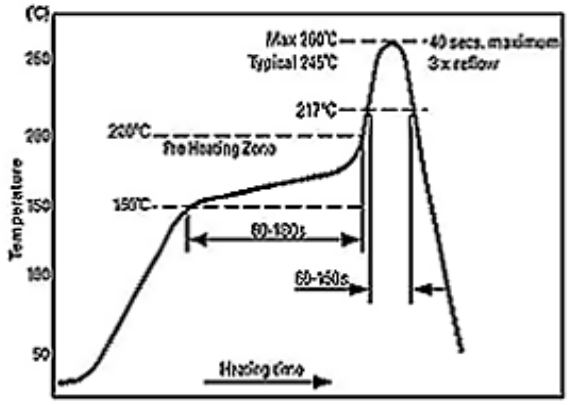
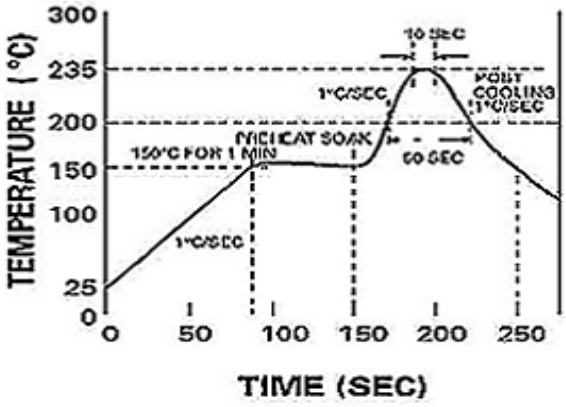


Figure 2

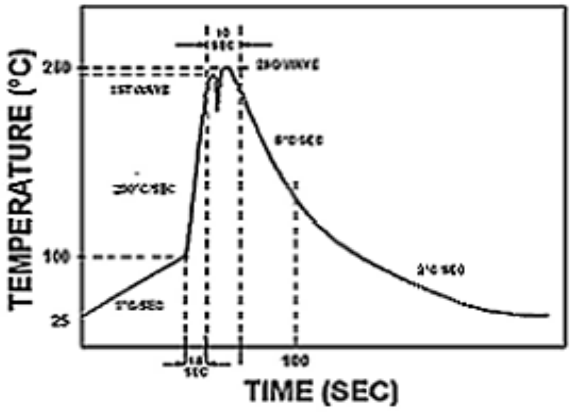


Reflow profiles in tabular form

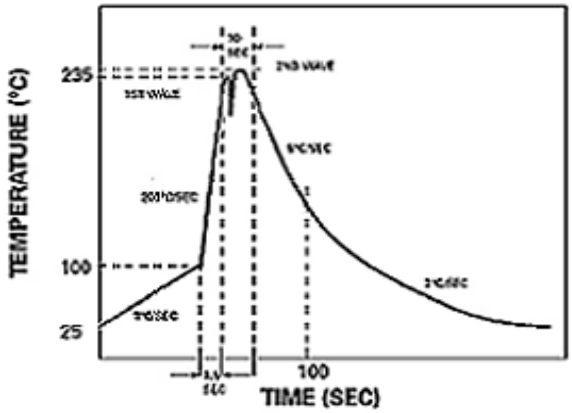
Profile Feature	Sn-Pb System	Pb-Free System
Average Ramp-Up Rate	~3°C/second	~3°C/second
Preheat – Temperature Range – Time	 150-170°C 60-180 seconds	 150-200°C 60-180 seconds
Time maintained above: – Temperature – Time	 200°C 30-50 seconds	 217°C 60-150 seconds
Peak Temperature	235°C	260°C max.
Time within +0 -5°C of actual Peak	10 seconds	40 seconds
Ramp-Down Rate	3°C/second max.	6°C/second max.

Recommended Wave Solder Profiles

The Recommended solder Profile For Devices with Pb-free terminal plating where a Pb-free solder is used



The Recommended solder Profile For Devices with Pb-free terminal plating used with leaded solder, or for devices with leaded terminal plating used with leaded solder



Wave Profiles in Tabular Form

Profile Feature	Sn-Pb System	Pb-Free System
Average Ramp-Up Rate	~200°C/second	~200°C/second
Heating rate during preheat	Typical 1-2, Max 4°C/sec	Typical 1-2, Max 4°C/Sec
Final preheat Temperature	Within 125°C of Solder Temp	Within 125°C of Solder Temp
Peak Temperature	235°C	260°C max.
Time within +0 -5°C of actual Peak	10 seconds	10 seconds
Ramp-Down Rate	5°C/second max.	5°C/second max

Recommended Product Storage Environment for Discrete Semiconductor Devices

This storage environment assumes that the Diodes and transistors are packed properly inside the original packing supplied by CDIL.

- Temperature 5 °C to 30 °C
- Humidity between 40 to 70 %RH
- Air should be clean.
- Avoid harmful gas or dust.
- Avoid outdoor exposure or storage in areas subject to rain or water spraying .
- Avoid storage in areas subject to corrosive gas or dust. Product shall not be stored in areas exposed to direct sunlight.
- Avoid rapid change of temperature.
- Avoid condensation.
- Mechanical stress such as vibration and impact shall be avoided.
- The product shall not be placed directly on the floor.
- The product shall be stored on a plane area. They should not be turned upside down. They should not be placed against the wall.

Shelf Life of CDIL Products

The shelf life of products is the period from product manufacture to shipment to customers. The product can be unconditionally shipped within this period. The period is defined as 2 years.
If products are stored longer than the shelf life of 2 years the products shall be subjected to quality check as per CDIL quality procedure.
The products are further warranted for another one year after the date of shipment subject to the above conditions in CDIL original packing.

Floor Life of CDIL Products and MSL Level

When the products are opened from the original packing, the floor life will start.
For this, the following JEDEC table may be referred:

JEDEC MSL Level		
Level	**Time**	**Condition**
1	Unlimited	≤30 °C / 85% RH
2	1 Year	≤30 °C / 60% RH
2a	4 Weeks	≤30 °C / 60% RH
3	168 Hours	≤30 °C / 60% RH
4	72 Hours	≤30 °C / 60% RH
5	48 Hours	≤30 °C / 60% RH
5a	24 Hours	≤30 °C / 60% RH
6	Time on Label(TOL)	≤30 °C / 60% RH

Customer Notes

Component Disposal Instructions

1. CDIL Semiconductor Devices are RoHS compliant, customers are requested to please dispose as per prevailing Environmental Legislation of their Country.
2. In Europe, please dispose as per EU Directive 2002/96/EC on Waste Electrical and Electronic Equipment (WEEE).

Disclaimer

The product information and the selection guides facilitate selection of the CDIL's Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished in the Data Sheet and on the CDIL Web Site/CD are believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Semiconductor Devices or incorporated in their end products), in any life saving/support appliances or systems or applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).
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